

APPLICATION DATA SHEET

APPLICATION INFORMATION

Application Type::	REGULAR
Subject Matter::	UTILITY
CD-ROM or CD-R?:	NONE
Title::	METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE INCLUDING PROCESS FOR IMPLANTING IMPURITIES INTO SUBSTRATE VIA MOS TRANSISTOR GATE ELECTRODE AND GATE INSULATION FILM
Attorney Docket Number::	240800US-2S DIV
Total Drawing Sheets::	12

INVENTOR INFORMATION

Applicant Authority Type::	INVENTOR
Primary Citizenship Country::	JAPAN
Status::	FULL CAPACITY
Given Name::	Norihisa
Family Name::	ARAI
City of Residence::	Omiya-shi
Country of Residence::	JAPAN
Street of Mailing Address::	1-1 Shibaura 1-chome
City of Mailing Address::	Minato-ku
State or Province of Mailing Address::	Tokyo
Country of Mailing Address::	JAPAN
Postal or Zip Code of Mailing Address::	105-8001

CORRESPONDENCE INFORMATION

Correspondence Customer Number::	22850
----------------------------------	-------

REPRESENTATIVE INFORMATION

Representative Customer Number::	22850
----------------------------------	-------

DOMESTIC PRIORITY INFORMATION

Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This Application	Division of	09/886,980	06/25/01

FOREIGN PRIORITY INFORMATION

Application Number:	Country::	Filing Date::	Priority Claimed::
2000-191589	Japan	06/26/00	YES